



● Product Summary

●  $V_{DSS} = -20V, I_D = -2.8A$

$R_{DS(on)}$  80mΩ@-2.5V(Typ)

110mΩ@-4.5V(Typ)

- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Application

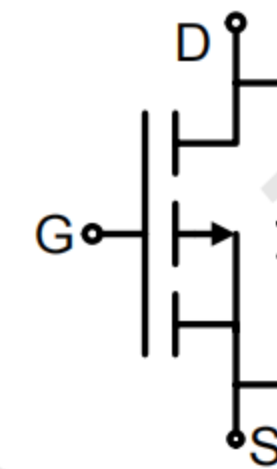
- PWM applications
- Load switch
- Power management

Package and Pin Configuration

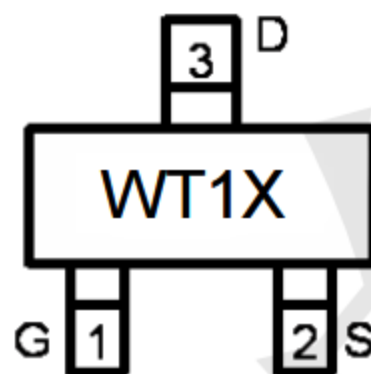
SOT-23



Circuit diagram



Marking:



Marking: WTIX  
 "WTI" is part number, fixed  
 "X" is internal code

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	±8	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_D$	-2.8	A
	$I_{DM}$	-10	A
Maximum Power Dissipation	$P_D$	1.25	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	°C/W
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**ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-20V, V_{GS}=0V$			-1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 8V, V_{DS}=0V$			$\pm 100$	nA
<b>ON CHARACTERISTICS (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.45		-1	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-2.8A$		80	100	
		$V_{GS}=-2.5V, I_D=-2A$		110	150	
Forward Transconductance	$g_{FS}$	$V_{DS}=-5V, I_D=-2.8A$		9		S
<b>DYNAMIC CHARACTERISTICS (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, V_{GS}=0V, F=1.0MHz$		1160		PF
Output Capacitance	$C_{oss}$			210		PF
Reverse Transfer Capacitance	$C_{rss}$			125		PF
<b>SWITCHING CHARACTERISTICS (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, I_D=-2.8A, V_{GS}=-4.5V, R_{GEN}=3\Omega$		13.6	27.2	nS
Turn-on Rise Time	$t_r$			8.6	17.2	nS
Turn-Off Delay Time	$t_{d(off)}$			73.6	147.2	nS
Turn-Off Fall Time	$t_f$			34.6	69.2	nS
Total Gate Charge	$Q_g$	$V_{DS}=-10V, I_D=-2.8A, V_{GS}=-4.5V$		9.6	12.7	nC
Gate-Source Charge	$Q_{gs}$			1.1		nC
Gate-Drain Charge	$Q_{gd}$			2.6		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-0.75A$			-1.2	V
Diode Forward Current (Note 2)	$I_S$				-2.8	A



Typical Electrical and Thermal Characteristics

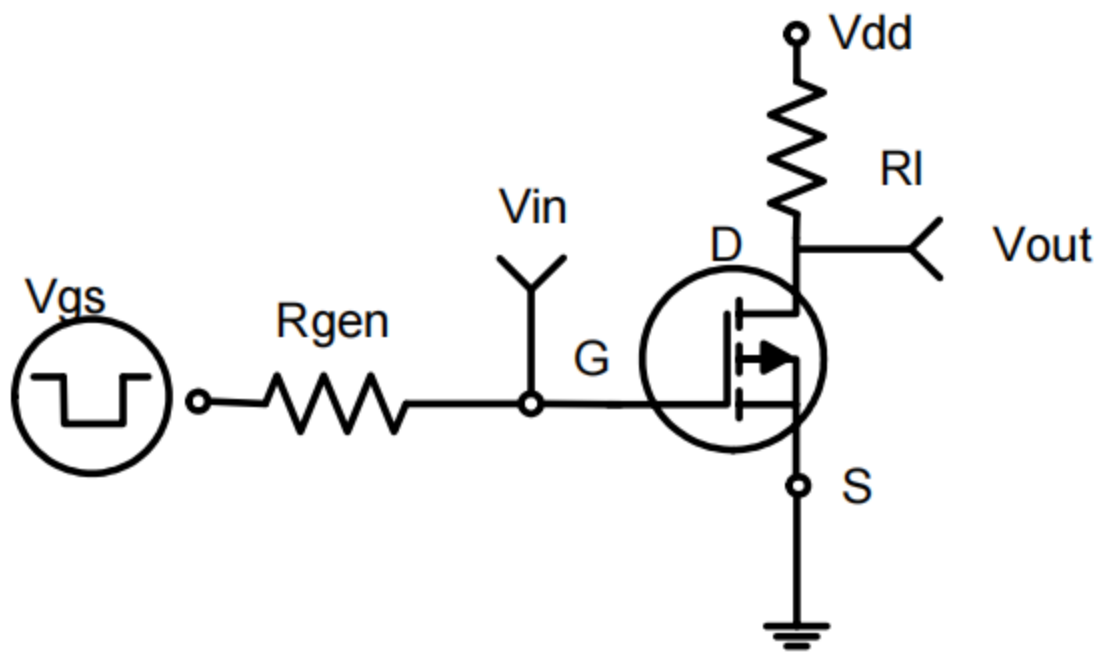


Figure 1: Switching Test Circuit

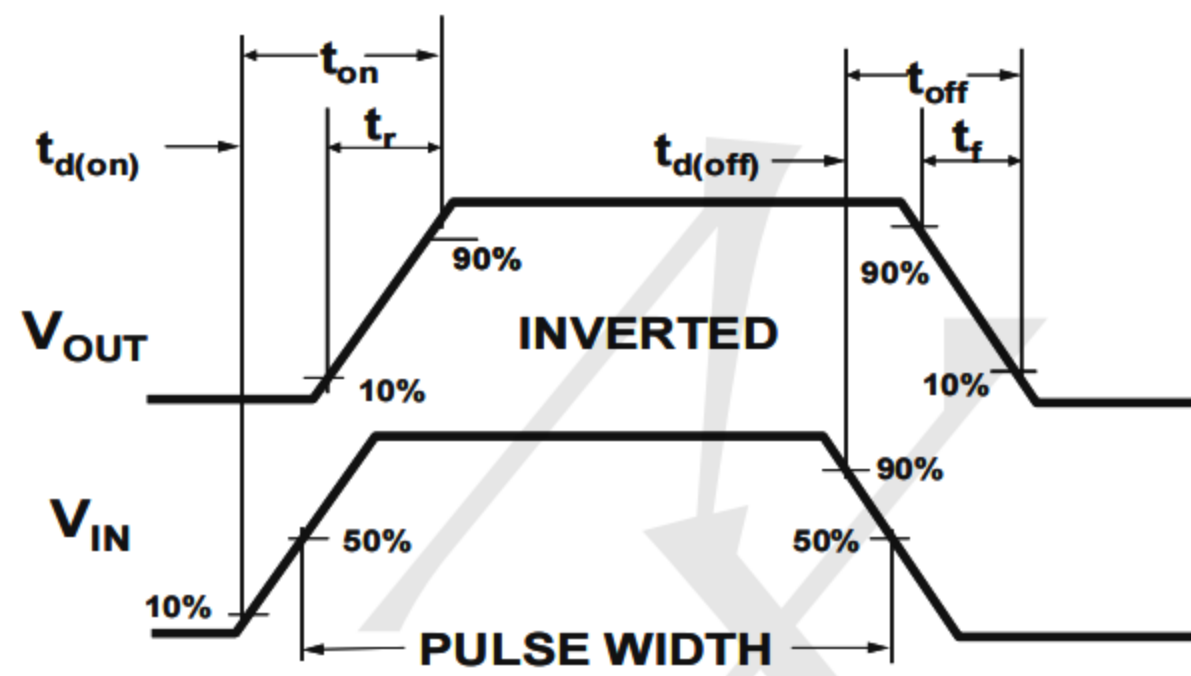


Figure 2: Switching Waveforms

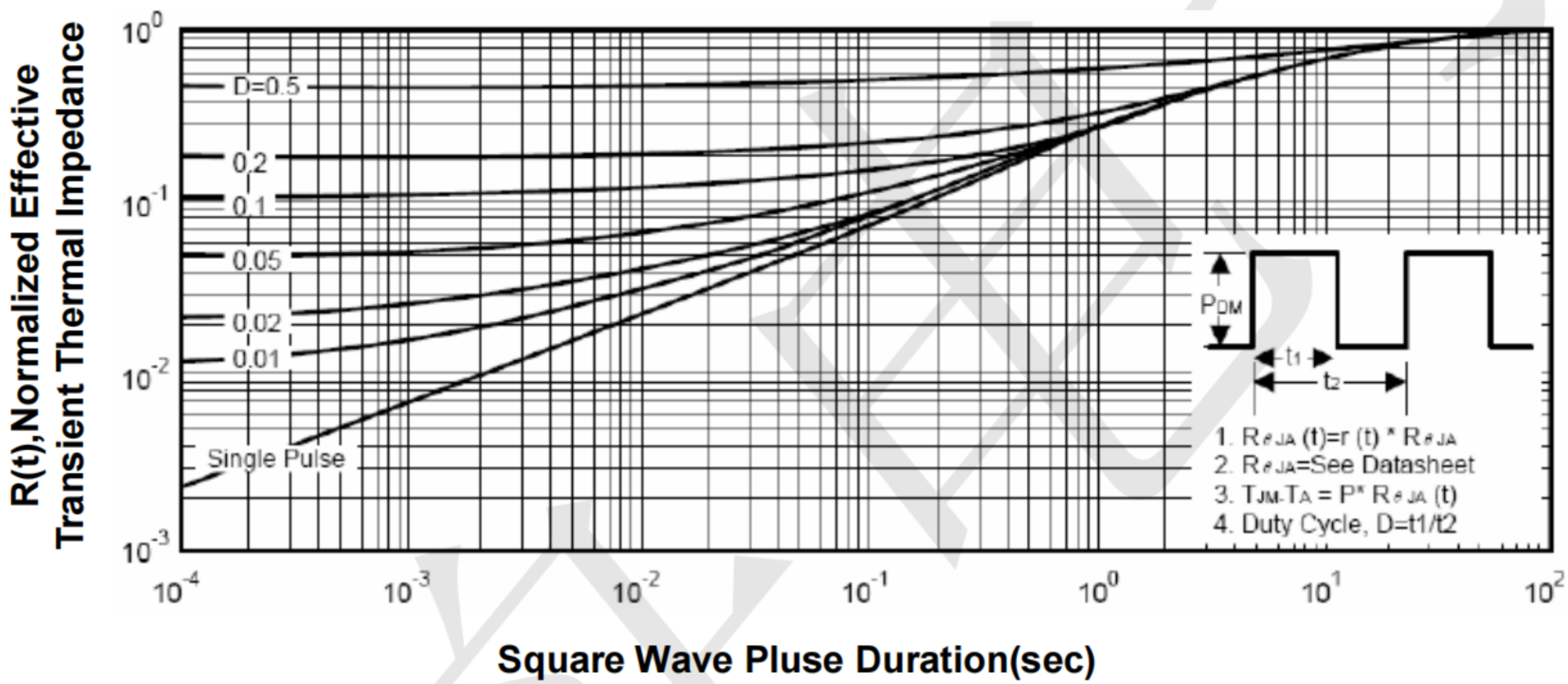
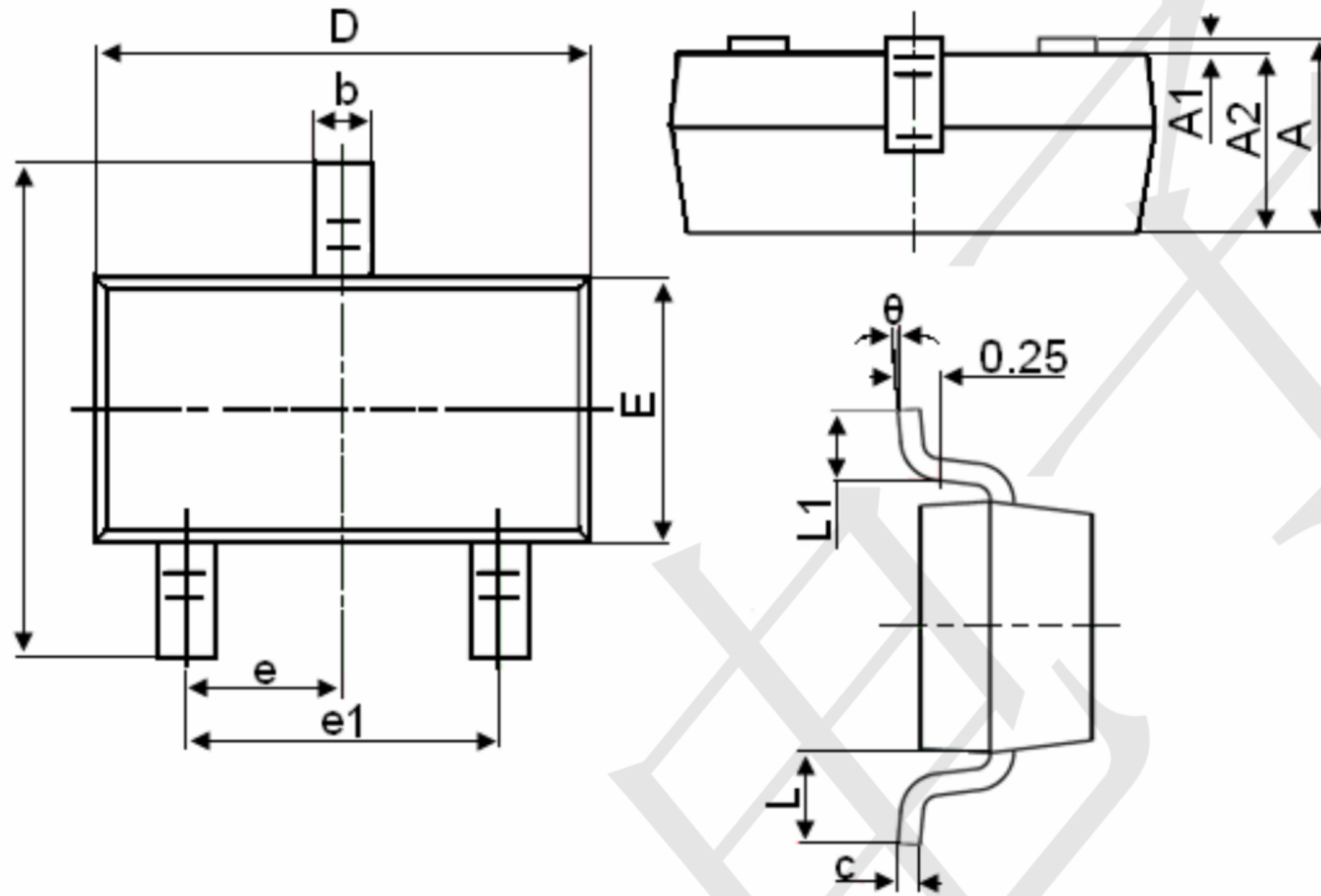


Figure 3: Normalized Maximum Transient Thermal Impedance



SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
$\theta$	0°	8°